

ABSTRACT OF THE DISCLOSURE

A method for controlling the top width of a trench. A
conductive layer is formed on the trench over the substrate,
forming an interlayer over a part thereof, above the conductive
5 layer. A sacrifice layer is formed on the trench sidewall above
the interlayer, and the interlayer is removed to expose the trench
sidewall above the conductive layer and the sacrifice layer,
such that the exposed trench sidewalls are oxidized. Thus, the
sacrifice layer on the trench sidewall reduces the top width
10 of the trench. In the oxidization process, silicon oxide is
formed on the sacrifice layer and the exposed trench sidewall,
such that upper width of the trench will is not increased during
subsequent wet etching.